

# Bootstrap Network Analysis: Focusing on the Integrated Bootstrap Functionality

## About this document

### Scope and purpose

The purpose of this document is to develop the bootstrap sizing theory and practice, while focusing in particular on topologies where the gate driver IC features integrated bootstrap functionality.

### Intended audience

The intended audiences for this document are design engineers, technicians, and developers of electronic systems.

## Table of contents

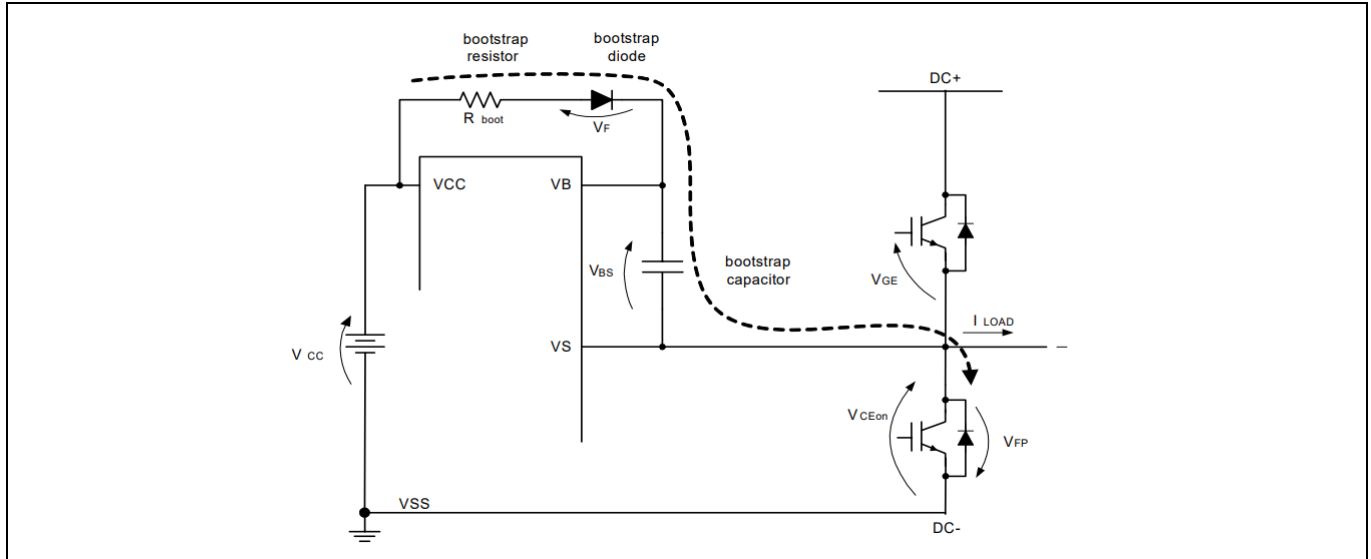
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## Introduction

### 1 Introduction

One of the most widely used methods to supply power to the high-side drive circuitry of a gate driver IC is the bootstrap power supply. The bootstrap power supply consists of a bootstrap diode and a bootstrap capacitor; this circuit is illustrated in Figure 1.



**Figure 1** bootstrap power supply

This method has the advantage of being both simple and low-cost. However, the requirement to refresh the charge on the bootstrap capacitor may result in limitations on the power converter's duty-cycle and the power switch's on-time. Proper capacitor and bootstrap resistance selection can drastically reduce these limitations.

The maximum voltage that the bootstrap capacitor (VBS) can reach is dependent on the elements of the bootstrap circuit shown in Fig. 1. The voltage drop across RBOOT, VF of the bootstrap diode, the drop across the low-side switch (VCEON or VFP, depending on the direction of current flow through the switch), and if present, the drop across a shunt resistor (not shown in Fig. 1) placed between the low-side switch's emitter and the DC-rail, all need to be considered.

The intent of this document is to develop the bootstrap sizing theory and practice, while focusing in particular on topologies where the gate driver IC features the integrated the bootstrap "diode"<sup>1</sup>.

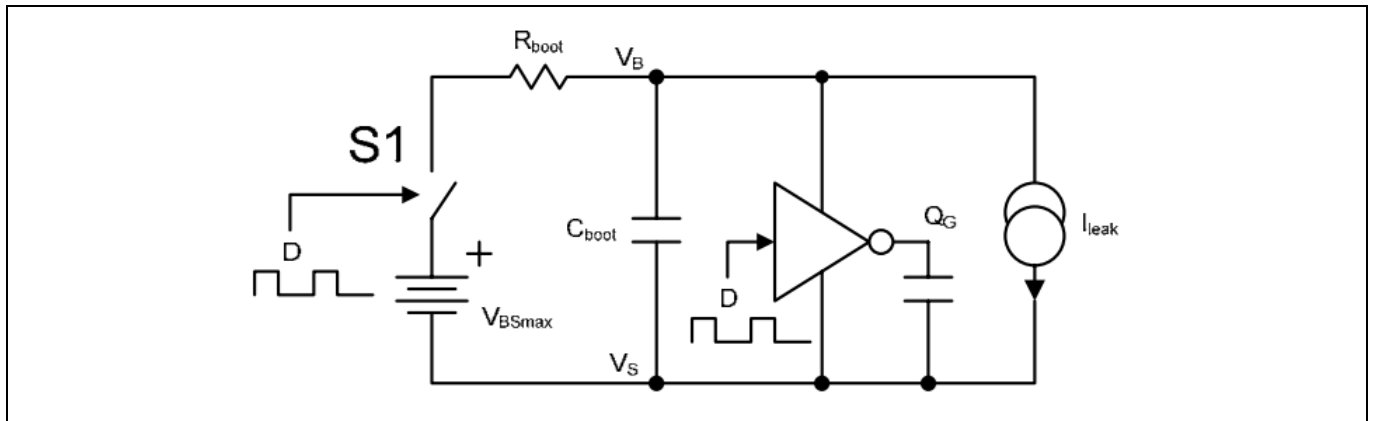
<sup>1</sup> The integrated bootstrap "diode" is described in this document in a simplified way by means of a resistor and an ideal switch in series. It may also be referenced as "bootstrap FET" as reflecting the real physical implementation in the silicon design.

## Theoretical considerations about the bootstrap topology

### 2 Theoretical considerations about the bootstrap topology

Some preliminary considerations need to be understood before examining the details of sizing the bootstrap circuit that is used in the half-bridge topology. The following simplified schematic can aid to develop this understanding (see Figure 2).

This representation of the bootstrap circuit (as shown in Fig. 2) eases the computation of the  $V_{BS}$  behavior as a function of the S1 switch state, or, as a function of its duty cycle ( $D = \text{duty cycle} = T_{ON}/T \equiv 1 - D^*$ )<sup>1</sup>, gate charge, leakage currents, and bootstrap resistor and capacitor.



**Figure 2** Simplified bootstrap schematic

$V_{BSMAX}$ , in general, represents the supply voltage ( $V_{CC}$  in Figure 1) plus or minus the bootstrap circuit's static drops.

It is important to understand that in the discussion that follows, the duty cycle of switch S1 is assumed to have reached steady state and will remain constant. This implies that the formulas reflect results that are valid considering the duty cycle is constant in time.

Later, some important considerations will then be derived while dealing with the "AC" response of the system (i.e., as duty cycle varies in time).

#### "Static" equations: $V_{BS}$ behavior in one PWM cycle:

The voltage ( $V_{BS}$ ) that develops across the bootstrap capacitor ( $C_{BOOT}$ ) is, in general, characterized by two contributions (according to Fig. 2). The first is represented by the voltage drop caused across the bootstrap resistor during the period in which the ideal switch (S1) is on ( $T_{ON}$ ). The second is a superimposed ripple, characteristic of the switching nature of the system; the magnitude of the AC ripple is primarily determined by the sizing of the bootstrap capacitor and can be calculated when S1 is off ( $T_{OFF}$ ). For the remainder of this discussion,  $V_{BSMAX}$  is defined as the maximum obtainable value for  $V_{BS}$ ; this is represented by the  $V_{BSMAX}$  generator in Figure 2.

#### 2.1 Bootstrap resistor contribution

The total charge that has to be supplied to the circuit by the supply ( $V_{BSMAX}$ ) during the switching period ( $T_S$ ) is shown in Eq.1.

$$Q_{TOT}^* = Q_G^* + I_{leak} \cdot T_S$$

<sup>1</sup>  $T_{ON}$  is the on time of the switch, which represents the time while the gating signal of the low-side IGBT is active.

## Theoretical considerations about the bootstrap topology

### Equation 1

The variable  $Q_G$  is defined as the total amount of charge needed by the gate of the power device and the gate driver level shifter, and  $I_{LEAK}$  takes into account the DC current that has to be supplied to the gate driver high side circuitry.

Considering that S1 is driven by a PWM waveform, and that charge is provided through the bootstrap resistor only during the  $T_{ON}$  time, then the average current flowing through the bootstrap resistor is as calculated in Eq.2.

$$\bar{I} = \frac{Q_G^* + I_{leak} \cdot T_S}{T_{on}} = \frac{Q_G^* \cdot f + I_{leak}}{D}$$
$$\left(f = \frac{1}{T_S}; D = \frac{T_{on}}{T_S}\right)$$

### Equation 2

The average voltage drop across  $R_{BOOT}$  is then defined by the Eq. 3.

$$V_{Rboot} = \frac{Q_G^* \cdot f + I_{leak}}{D} \cdot R_{boot}$$

### Equation 3

## 2.2 Bootstrap capacitor contribution

The total charge supplied by the bootstrap capacitor to the high-side circuitry can be calculated by Eq. 4.

$$Q_{TOT} = Q_G^* + I_{leak} \cdot T_{off} = Q_G^* + I_{leak} \cdot (1 - D) \cdot T_S$$

### Equation 4

The ripple amplitude for  $V_{BS}$  can be determined by considering Eq. 5.

$$\Delta V_{BS} = \frac{Q_{TOT}}{C_{boot}}$$

### Equation 5

The shape of  $V_{BS}$  as a function of time is represented in Figure 3, where the various contributions have been distinguished. The calculation for  $V_{drop}$  (as shown in Fig. 3) given by Eq. 6.

$$V_{drop} = V_{Rboot} + \Delta V_{BS}/2^1$$

<sup>1</sup>  $V_{drop}$  represents the drop of  $V_{BS}$  from the maximum value that it can reach ( $V_{BSMAX}$ ) considering all the elements of the bootstrap circuit, that are not mentioned in this simplified description. These elements will be described further ahead.

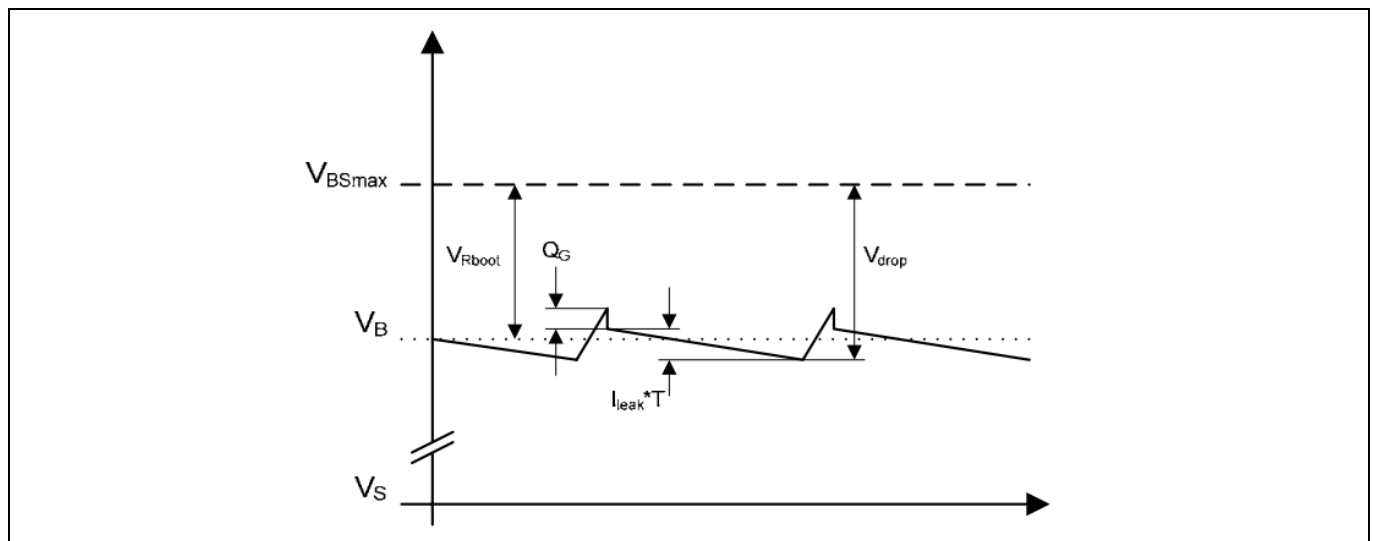
## Theoretical considerations about the bootstrap topology

### Equation 6

The above mentioned formula is valid only when the duty cycle is low enough such that  $V_{Rboot}$  becomes greater than  $\Delta V_{BS}/2$ . This happens approximately when the recharge time is enough to fully charge the bootstrap capacitor (for this calculation, we will assume the capacitor is fully charged after a  $\Delta t$  of 4 time constants). Equation 7 shows the duty cycle's boundary condition.

$$D < \frac{4 \cdot R_{boot} \cdot C_{boot}}{T_S}$$

### Equation 7



**Figure 3**  $V_{BS}$  waveform

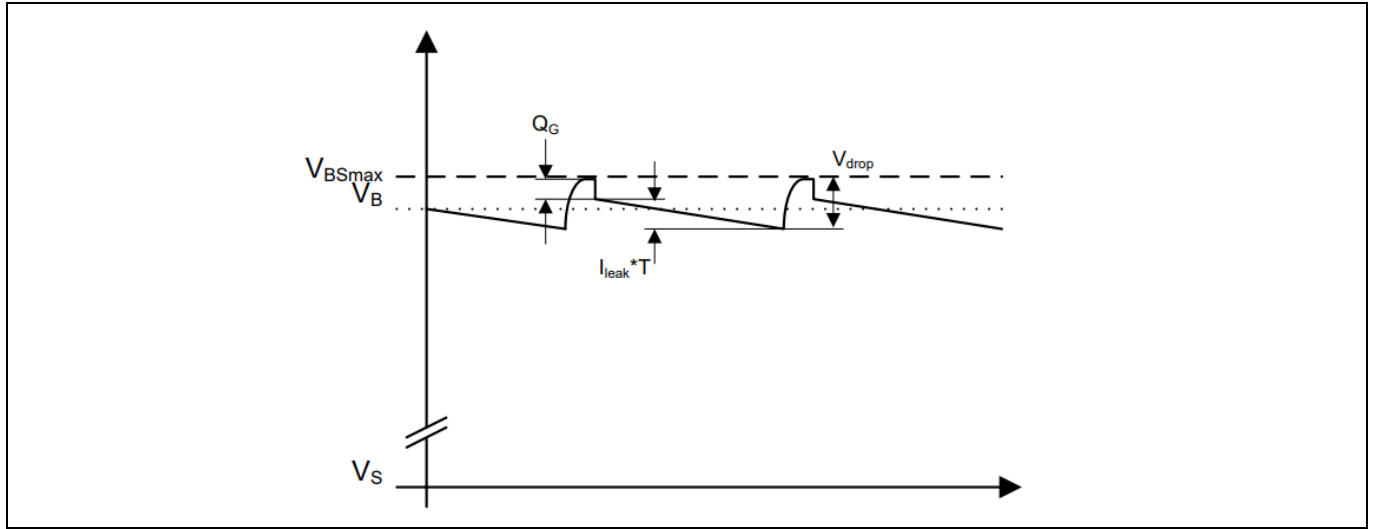
Whenever  $D \gg \frac{4 \cdot R_{boot} \cdot C_{boot}}{T_S}$ , Eq. 6 is no longer valid and  $V_{drop}$  becomes equal to  $\Delta V_{BS}$  as shown in Fig. 4.

$$V_{drop} = \Delta V_{BS}$$

### Equation 8

An important consideration that must be made is that while the  $V_{BS}$  ripple depends only on the bootstrap capacitor, the average voltage drop ( $V_{drop}$ ) from the maximum reachable  $V_{BS}$  ( $V_{BSMAX}$ ) depends only on the bootstrap resistor.

## Theoretical considerations about the bootstrap topology



**Figure 4**  $V_{drop}$  for  $D \gg \frac{4 \cdot R_{boot} \cdot C_{boot}}{T_S}$

It should be noted that even with a reasonably large bootstrap capacitor (to make  $\Delta V_{BS}$  negligible)  $V_{Rboot}$  drop may be large. This contribution to the  $V_{BS}$  drop fixes a limit to the minimum acceptable duty cycle for a given bootstrap resistor. Equation 9 shows  $D_{MIN}$  while neglecting the  $\Delta V_{BS}$  contribution and that  $V_{drop}$  is the maximum acceptable drop from the supply.

$$D_{MIN} = \frac{Q_G^* \cdot f + I_{leak}}{V_{drop}} \cdot R_{boot}$$

### Equation 9

Example:

$Q_G^* = 40 \text{ nC}$ ,  $f = 20 \text{ kHz}$ ,  $I_{leak} = 200 \mu\text{A}$ ,  $R_{boot} = 220 \Omega$ ,  $V_{drop} = 2 \text{ V}$  ( $V_{BS} = V_{CC} - V_{drop} = 13 \text{ V}$ ). The minimum acceptable duty cycle will be 11%.

A simulation has been performed using the following parameters and the results are shown in Figs. 5 and 6. For this simulation,  $R_{boot} = 220 \Omega$ ,  $Q_G = 40 \text{ nC}$ ,  $I_{leak} = 200 \mu\text{A}$ ,  $f = 1/T_S = 20 \text{ kHz}$ , the  $D_{MIN}$  duty cycles are either  $D=10\%$  or  $D=30\%$ , and  $C_{boot} = 47 \text{ nF}$  or  $1 \mu\text{F}$  (pre-charged to  $V_{BSmax} = 15 \text{ V}$ ).

Below is an example of the calculation for the case where  $C_{boot}$  equals  $47 \text{ nF}$  and the duty cycle is 10%.

$$D = 10\% \ll \frac{4 \cdot R_{boot} \cdot C_{boot}}{T_S} = \frac{4 \cdot 220 \Omega \cdot 1 \mu\text{F}}{50 \mu\text{s}} = 82.7\%$$

### Equation 10

then

$$V_{drop} = V_{Rboot} + \Delta V_{BS}/2$$

### Equation 11

The expected  $V_{Rboot}$  for the worst case ( $D=10\%$ ) is:

## Theoretical considerations about the bootstrap topology

$$V_{Rboot} = \frac{40 \text{ nC} \cdot 20 \text{ kHz} + 200 \mu\text{A}}{10\%} \cdot 220 \Omega = 2.2 \text{ V}$$

### Equation 12

The expected ripple ( $C_{boot} = 47 \text{ nF}$ ) is:

$$\Delta V_{BS} = \frac{40 \text{ nC} + 200 \mu\text{A} \cdot (1 - 10\%) \cdot 50 \mu\text{s}}{47 \text{ nF}} = 1 \text{ V}$$

### Equation 13

$$V_{drop} = V_{Rboot} + \Delta V_{BS}/2 = 2.7 \text{ V} \Rightarrow V_{BS} = 12.3 \text{ V}$$

### Equation 14

#### Dynamic response:

The simulations plotted in Figure 5 and 6 are shown with  $C_{boot}$  equal to 47 nF or 1  $\mu\text{F}$  and the duty cycle equal to 10% or 30%. The green and yellow curves represent  $V_{BS}$  with a 47 nF bootstrap capacitor. The purple and red curves represent  $V_{BS}$  with a 1  $\mu\text{F}$  bootstrap capacitor.

Figure 6 shows the effect of the different bootstrap capacitors, which affects only the  $V_{BS}$  ripple (the average value is, in fact, kept constant).

Figure 5 shows the step response of the system starting with the bootstrap capacitor fully charged to 15 V ( $D=100\%$ ). In particular this picture shows that the average  $V_{BS}$  has a behavior that is similar to a single pole system with a time constant that is calculated in Eq. 15.

$$\tau = \frac{R_{boot} \cdot C_{boot}}{D}$$

### Equation 15

This relationship between the duty cycle and the step response of the system allows us to understand that for lower duty cycles, the time constant ( $\tau$ ) becomes larger (and thus the response is slower) and that for higher duty cycles, the response is faster.

This behavior works as an adaptive filter for changes in the duty cycle. This can be seen in a further simulation (see Fig. 7) in which a sinusoidal wave (40 Hz fundamental plus the 3<sup>rd</sup> harmonic) modulated duty cycle is fed to the circuit ( $T_S = 50 \mu\text{s}$ , electrical frequency =  $f_e$ ).

In Figure 5 the parameters are  $R_{boot} = 220 \Omega$ ,  $C_{boot} = 1 \mu\text{F}$  and  $D = 10\%$ .

$$\tau = \frac{220 \cdot 1 \mu\text{F}}{0.1} = 2.2 \text{ ms} \rightarrow f_\tau = \frac{1}{2\pi\tau} = 72 \text{ Hz}$$

### Equation 16

The combination of  $R_{boot} = 220 \Omega$ ,  $C_{boot} = 1 \mu\text{F}$  and  $D = 10\%$  is also shown.



## Theoretical considerations about the bootstrap topology

$$\tau = \frac{220 \cdot 1 \mu F}{0.3} = 733 \mu s \rightarrow f_{\tau} = \frac{1}{2\pi\tau} = 217 Hz$$

Equation 17

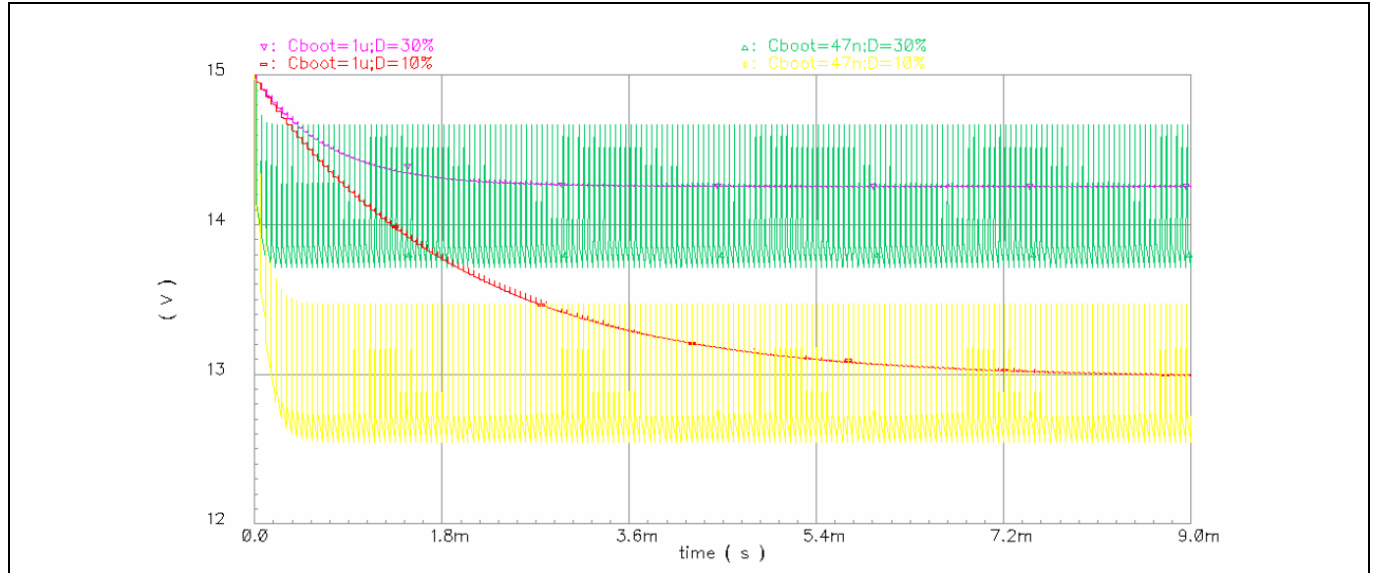


Figure 5 Bootstrap circuit parametric simulation: S1 duty cycle and bootstrap capacitor

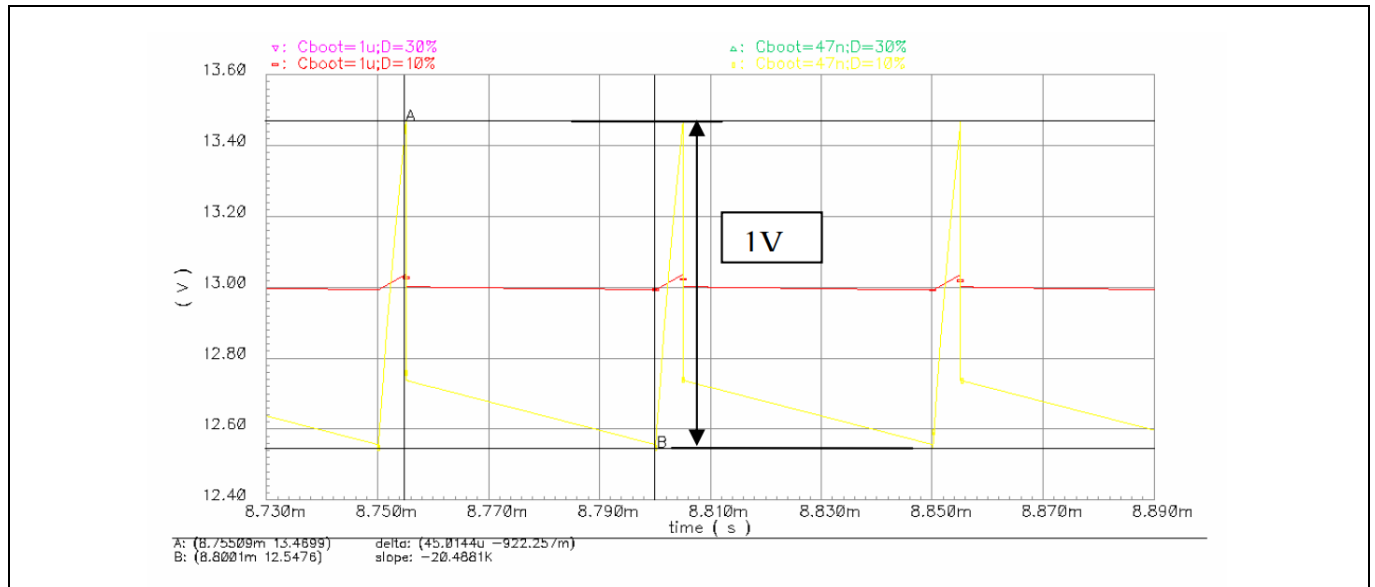
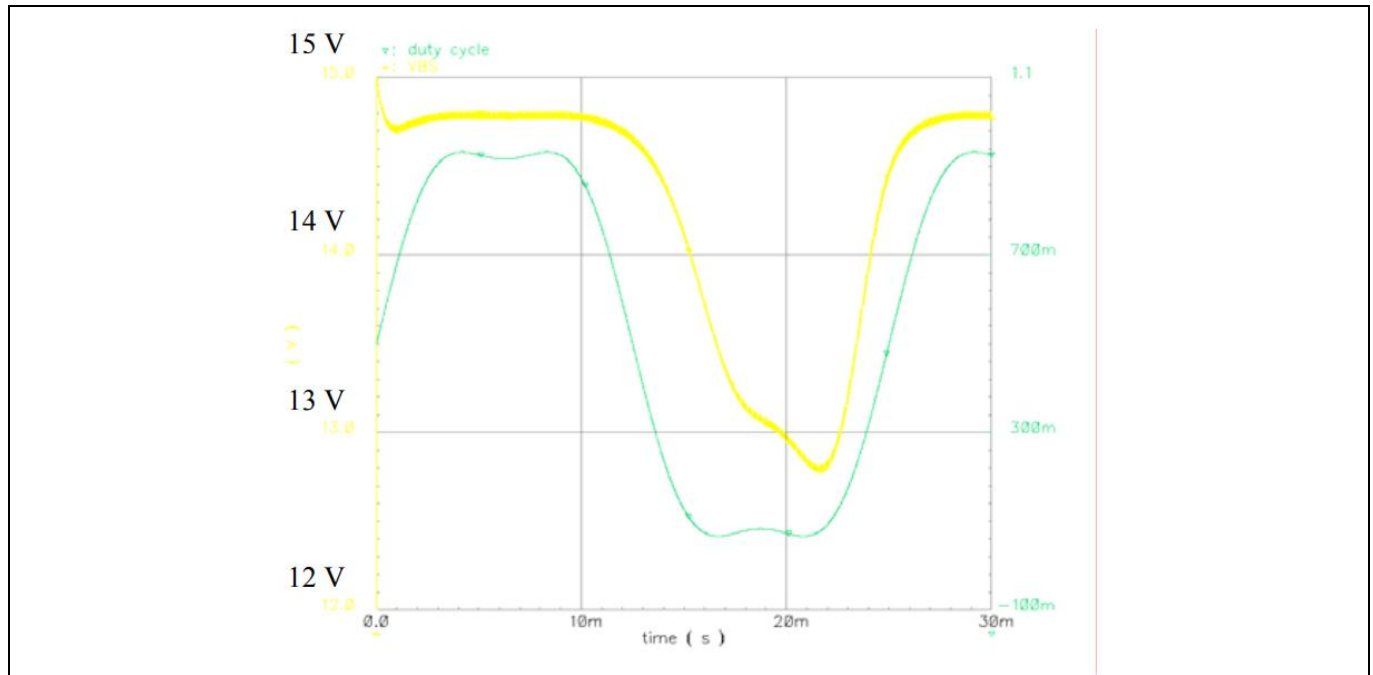


Figure 6 Ripple behavior for different  $C_{boot}$

## Theoretical considerations about the bootstrap topology



**Figure 7** 40 Hz Sine plus 3<sup>rd</sup> harmonic modulation of S1 duty cycle<sup>1</sup>

As a drawback,  $Q_{TOT} = Q_G^* + I_{leak} \cdot T_{off} = Q_G^* + I_{leak} \cdot (1 - D) \cdot T_S$  increases for low duty cycles. In this case, a larger bootstrap capacitor will do the job of keeping the ripple under control and increasing the average time constant.

The dynamic response of the system is of particular interest. Fig. 8 shows the expected (calculated)  $V_{BS}$  for different electrical frequencies. The duty cycle is represented as a function (sine + 3<sup>rd</sup> harmonic) of an angle (which is equal to  $2\pi f_e$ , where  $f_e$  is the electrical frequency of the rotor) which swings from  $0^\circ$  to  $360^\circ$ .

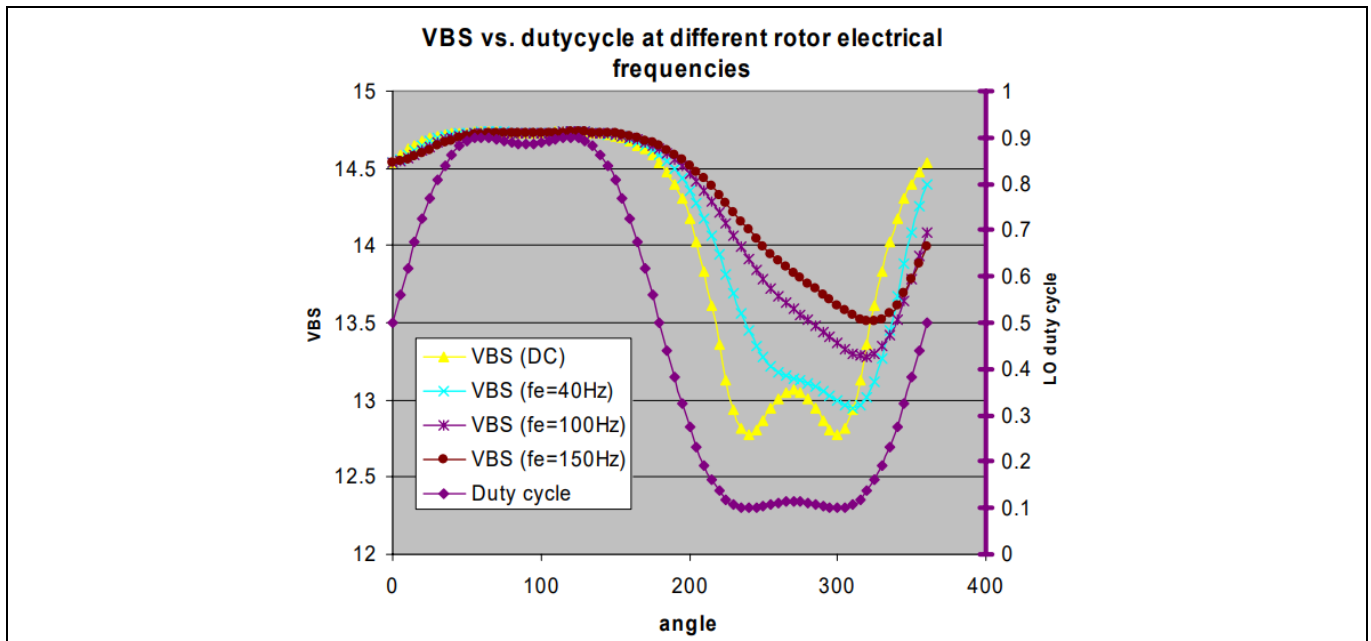
In the same plot,  $V_{BS}$  voltages that are obtained with different  $f_e$  are shown. An additional note to mention regarding this figure is that the yellow curve,  $V_{BS}$  (DC), represents the curve obtained when using the static equations mentioned previously (Eqs. 3, 5, 6, & 8). The cyan curve is obtained with  $f_e = 40$  Hz as in the simulation of Fig. 7.

<sup>1</sup> Same data as per previous pages:  $R_{boot} = 220 \Omega$ ,  $Q_G = 40$  nC,  $I_{leak} = 200 \mu A$ ,  $f = 1/T_S = 20$  kHz  
Application note

## Sizing the bootstrap circuit using the integrated bootFET

### 3 Sizing the bootstrap circuit using the integrated bootFET

As shown in Figure 1 the bootstrap circuit includes some components that must be taken into account when sizing the bootstrap resistor and capacitor. In the case of using a gate driver with integrated bootstrap functionality (e.g., those with an integrated bootstrap FET or bootstrap diode), the external bootstrap diode is not used (for most applications) and the voltage drop across the bootstrap FET (or internal bootstrap diode) replaces the  $V_F$  typically considered during circuit analysis. The other elements that must be considered include power switch (e.g., IGBT), the free wheeling diode in parallel with the switch, and any shunt resistors used on the DC- rail or in series with the low-side switch and the DC- rail.



**Figure 8 Expected  $V_{BS}$  drop at different rotor electrical frequencies**

Following the nomenclature used in the above paragraphs,  $V_{BSmax}$  (see Figure 2 and 5) can be computed as follows:

$$V_{BS\ max} = V_{CC} - V_{CE} \quad (\text{bootstrap FET})$$

**Equation 18**

or

$$V_{BS\ max} = V_{CC} - V_F - V_{CE} \quad (\text{bootstrap diode})$$

**Equation 19**

Where  $V_{CC}$  is the low-side supply,  $V_F$  is the forward drop of the bootstrap diode,  $V_{CE}$  can be either the voltage drop on the IGBT (when current is flowing into the power device) or the forward biased voltage drop of the freewheeling diode (in this case, it is a negative contribution which increases  $V_{BSMAX}$ ). In the worst case sizing,  $V_{CE}$  is represented by the  $V_{CEon}$  of the low-side IGBT.

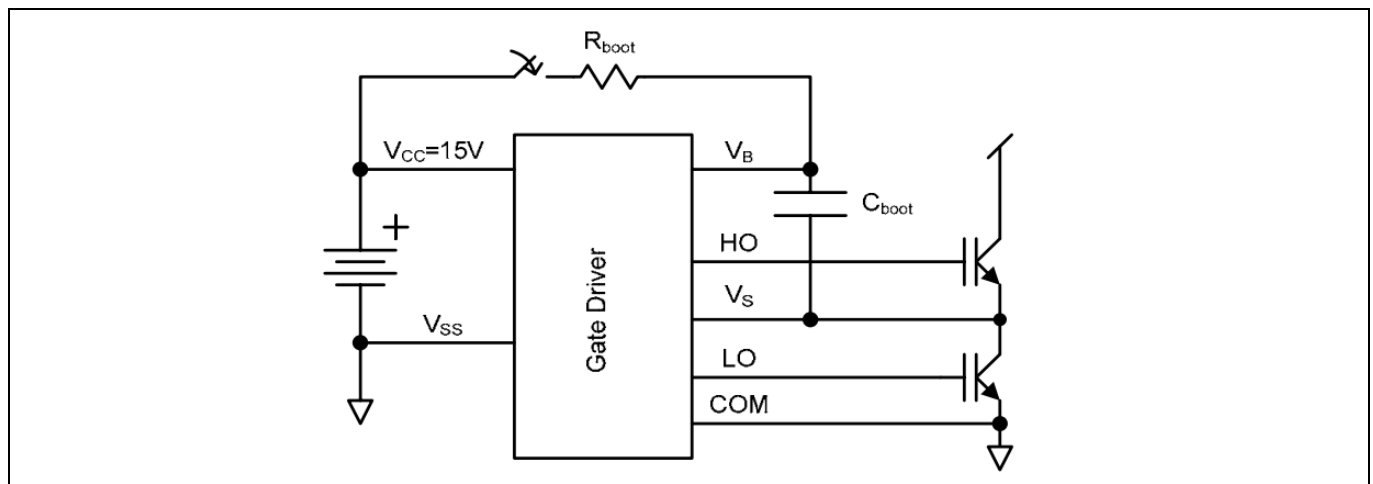
The following design example will consider a system as shown in Figure 9, where the bootstrap FET is represented by an ideal switch and a resistor.

## Sizing the bootstrap circuit using the integrated bootFET

The first step in sizing the bootstrap circuit is to determine the minimum voltage drop ( $V_{drop}$ ) when the high-side IGBT is on. Considering that a minimum gate voltage must be provided to the IGBT's gate ( $V_{GEmin}$ ),  $V_{drop}$  is the maximum possible voltage drop of the  $V_{BS}$  supply, and is defined by the following formula:

$$V_{drop} = V_{CC} - V_{GEmin} - V_{CEon}$$

**Equation 20**



**Figure 9 Bootstrap FET represented by ideal switch and  $R_{boot}$**

It should be noted that gate drivers from International Rectifier (now acquired by Infineon) are equipped with under voltage lock-out (UVLO) protection on the high-side gate drive where the  $V_{BS}$  voltage is monitored to ensure a minimum threshold; should the  $V_{BS}$  decrease below this threshold, the UVLO protection would engage and disable the gate driver IC. Therefore, the minimum  $V_{GE}$  should be greater than the high-side supply undervoltage negative going threshold ( $V_{BSUV-}$ ).

$$V_{GEmin} > V_{BSUV-}$$

**Equation 21**

The following factors that contribute to the discharge of the bootstrap capacitors voltage ( $V_{BS}$ ) during the time that the low-side switch is off must also be considered.

- IGBT required gate charge during turn-on ( $Q_G$ );
- IGBT gate-source leakage current ( $I_{LK\_GE}$ );
- Floating section quiescent current ( $I_{QBS}$ );
- Floating section leakage current ( $I_{LK}$ );
- Bootstrap diode reverse bias leakage ( $I_{LK\_DIODE}$ );
- Charge required by the internal level shifters ( $Q_{LS}$ );
- Bootstrap capacitor leakage current ( $I_{LK\_CAP}$ );
- High-side maximum on time ( $((1-D_{MIN}) \cdot T_S$  where  $D_{MIN}$  is the minimum duty cycle).

## Sizing the bootstrap circuit using the integrated bootFET

$I_{LK\_CAP}$  is only relevant when using an electrolytic capacitor and can be ignored if other types of capacitors are used. It is strongly recommend to use at least one low ESR ceramic capacitor (paralleling electrolytic and low ESR ceramic may result in an efficient solution).

The total amount of charge that is removed from the bootstrap capacitor during the time that the high-side device is referred to as  $Q_{TOT}$  (see Eq. 4) and can be calculated by Eq. 22.

$$\begin{aligned} Q_{TOT} &= Q_G + Q_{LS} + (I_{LK\_GE} + I_{QBS} + I_{LK} + I_{LK\_CAP}) \cdot (1 - D_{MIN}) \cdot T_S \\ &= Q_G^* + I_{LEAK} \cdot (1 - D_{MIN}) \cdot T_S \end{aligned}$$

### Equation 22

The bootstrap capacitor can be chosen by using  $C_{boot} > \frac{Q_{TOT}}{V_{drop}}$  and verifying that:

$$D_{MIN} > \frac{4 \cdot R_{boot} \cdot C_{boot}}{T_S}$$

### Equation 23

so that  $V_{drop} = \Delta V_{BS}$  (see Figure 4).

Let's suppose the above equation is not verifiable,  $V_{drop}$  may be calculated by  $V_{drop} = V_{Rboot} + \Delta V_{BS} / 2$ . Using the formula mentioned in Eq. 3 and the known value of  $V_{drop}$ ,  $V_{BS}$  can be determined by  $V_{BS\ min} = V_{CC} - V_{CEon} - V_{drop}$  while remembering the  $V_{GEmin}$  requirement.

## Test bench measurements with no load current

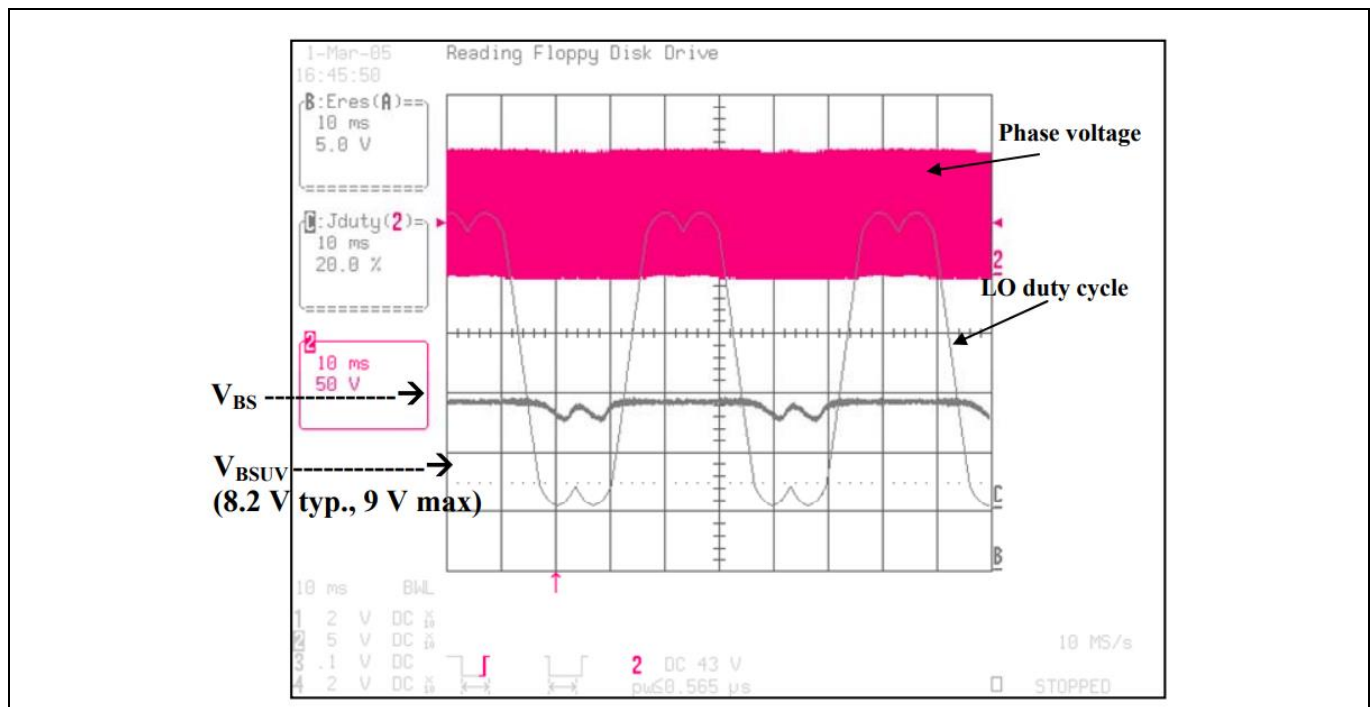
### 4 Test bench measurements with no load current

To provide a better example of the integrated bootstrap circuitry's behavior/performance, a comparison of some lab examples are included. There are three comparisons shown and include:

- 10  $\Omega$  bootstrap resistor and external bootstrap diode circuit
- Integrated bootstrap circuitry
- Parallel of integrated bootstrap circuitry and external bootstrap components

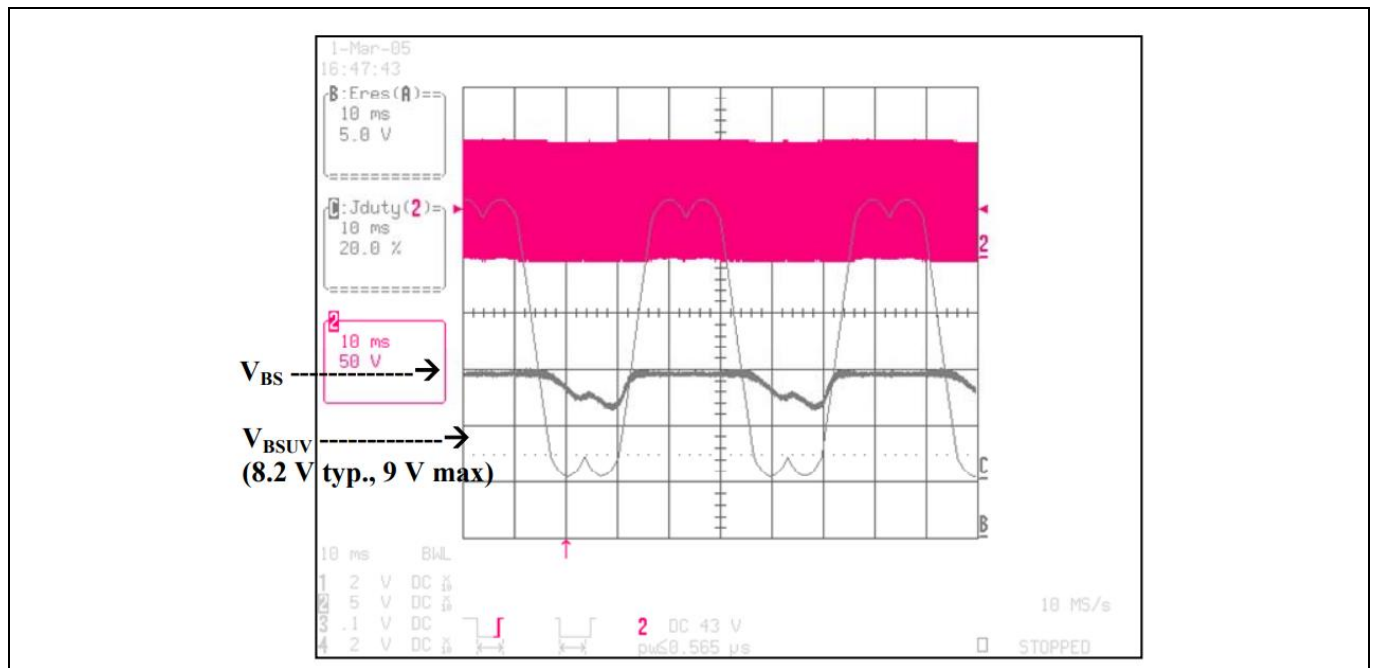
Test conditions:

- PWM=20 kHz
- $C_{boot}=1 \mu F$
- Fundamental=25 Hz
- Minimum pulse = 560 ns (modulation index=97.7%)
- No load current
- Gate driver IC: IR2136 (external bootstrap topology) or IRS2136D (integrated bootstrap)



**Figure 10** 10  $\Omega$  + diode external bootstrap circuit (560 ns min pulse)

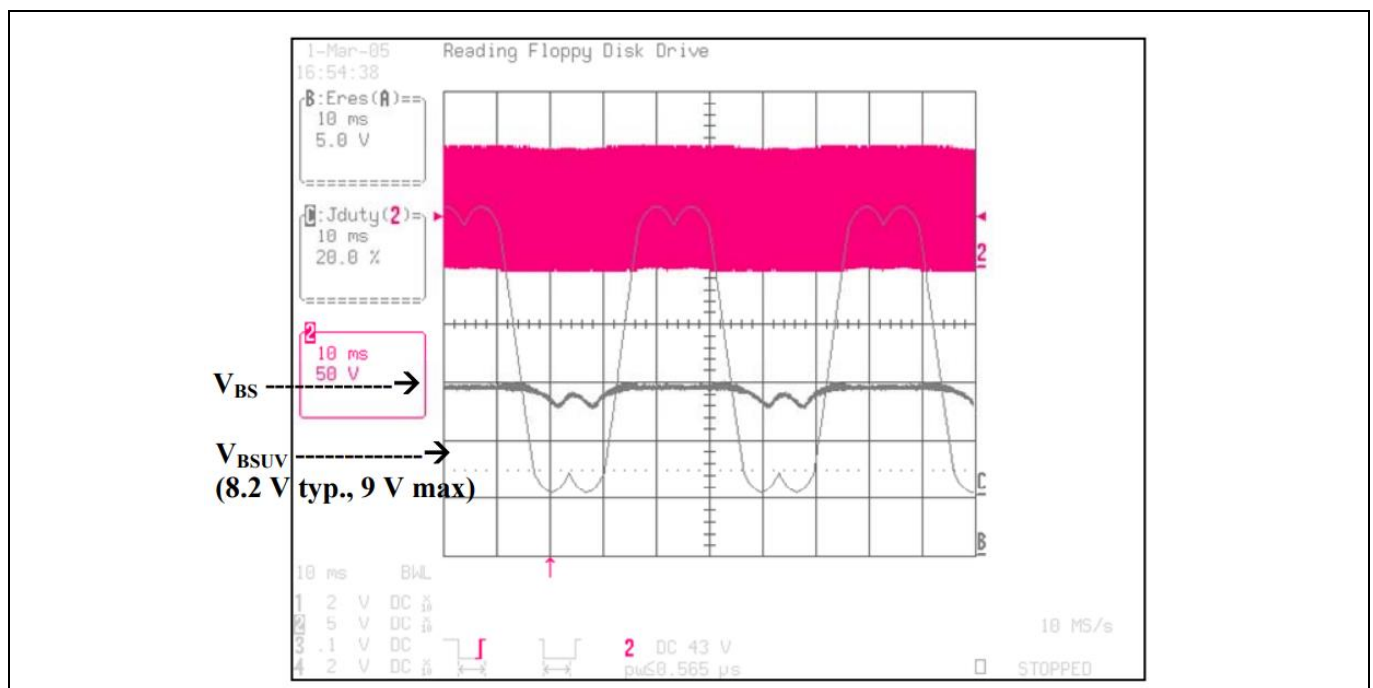
## Test bench measurements with no load current



**Figure 11 Integrated bootstrap circuitry (560 ns min pulse)**

It is interesting to note (see Fig. 11) the integrated bootstrap network provides a filtering effect at the 25 Hz fundamental frequency. In the same picture  $V_{BS}$  can be seen to reach nearly 15 V without losing the forward drop of the bootstrap diode.

In this second example, the minimum pulse is increased to 5  $\mu$ s and the modulation index decreased to 80%.



**Figure 12 Integrated bootstrap circuitry in parallel with external bootstrap components (560 ns min pulse)**

## Test bench measurements with no load current

Test conditions:

- PWM=20 kHz
- $C_{boot}=1\text{ }\mu\text{F}$
- Fundamental=25 Hz
- Minimum pulse = 5  $\mu\text{s}$  (modulation index=80%)
- No load current
- Gate driver IC: IR2136 (external bootstrap topology) or IRS2136D (integrated bootstrap)

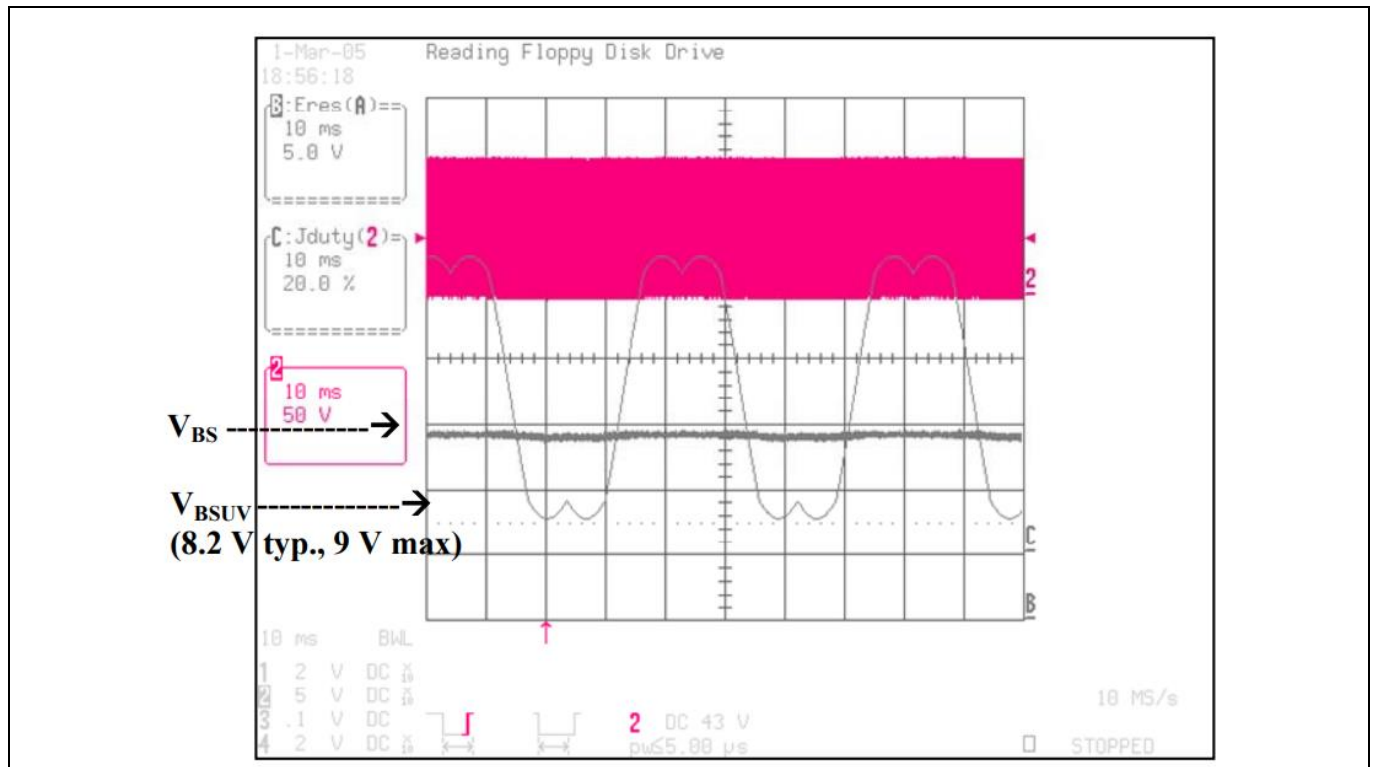
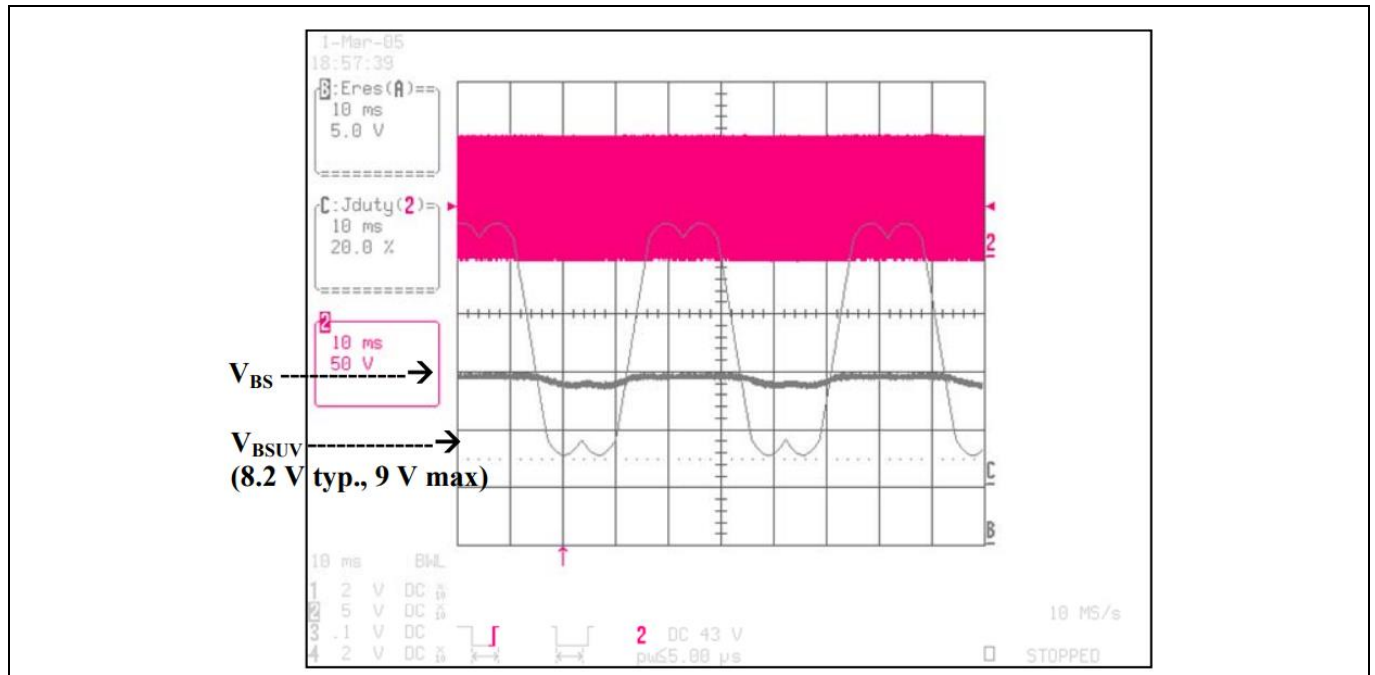


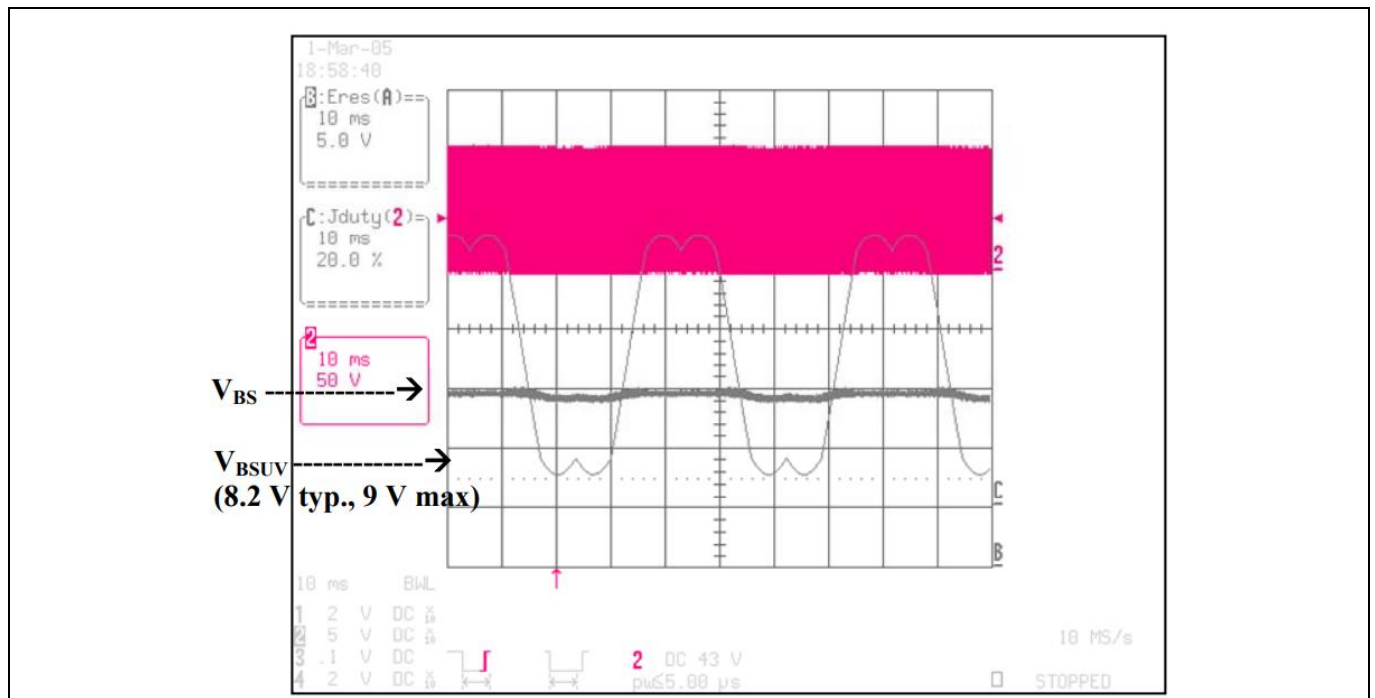
Figure 13 10  $\Omega$  resistor + diode external bootstrap circuit (5  $\mu\text{s}$  min pulse)



## Test bench measurements with no load current



**Figure 14** Integrated bootstrap circuitry (5  $\mu$ s min pulse)



**Figure 15** Integrated bootstrap circuitry in parallel with external Bootstrap components (5  $\mu$ s min pulse)

With a low modulation index, the integrated bootstrap circuitry provides results as good as those obtained with the external bootstrap circuit at 25 °C.

## Considering the bootstrap circuit for varying loads

### 5 Considering the bootstrap circuit for varying loads

In the examples shown above, the tests do not consider the effect of the current delivered (positive or negative) to the load. The effect of the load current influences the value of  $V_{BSMAX}$ . A description of this effect follows.

There are three different situations that can occur. The first is the case where  $I_{LOAD}$  is less than zero.

- $I_{LOAD} < 0$ ; the load current flows into the low-side IGBT and generates a given  $V_{CEon}$

$$V_{BSMAX} = V_{CC}(-V_F) - V_{CEon}$$

#### Equation 24

In this case, we find the lowest value for  $V_{BSMAX}$ . This represents the worst case for the sizing of the bootstrap capacitor. The low-side IGBT's  $V_{CEon}$  pulls up the  $V_S$  node and reduces the available voltage for charging the bootstrap supply. In the case of a circuit that uses a shunt resistor in series with the IGBT, its voltage drop may influence the result as well.

If we consider a small phase shift between the phase current and the phase voltage (a phenomenon that happens when the phase duty cycle is high and the bootstrap capacitor has more time to charge), depending on the magnitude of  $V_{CEon}$ , the induced voltage drop may be reduced.

In the second case, the load current is zero and the voltage drop across the switch can be neglected. This situation was discussed above in this document and happens during current zero crossings.

- $I_{LOAD} = 0$ ; the IGBT is not loaded while being on and  $V_{CE}$  can be neglected

$$V_{BSMAX} = V_{CC}(-V_F)$$

#### Equation 25

In the third case, the load current is positive and the voltage drop across the switch is due to the drop that results from the freewheeling diode.

- $I_{LOAD} > 0$ ; the load current flows through the freewheeling diode

$$V_{BSMAX} = V_{CC}(-V_F) - V_{FP}$$

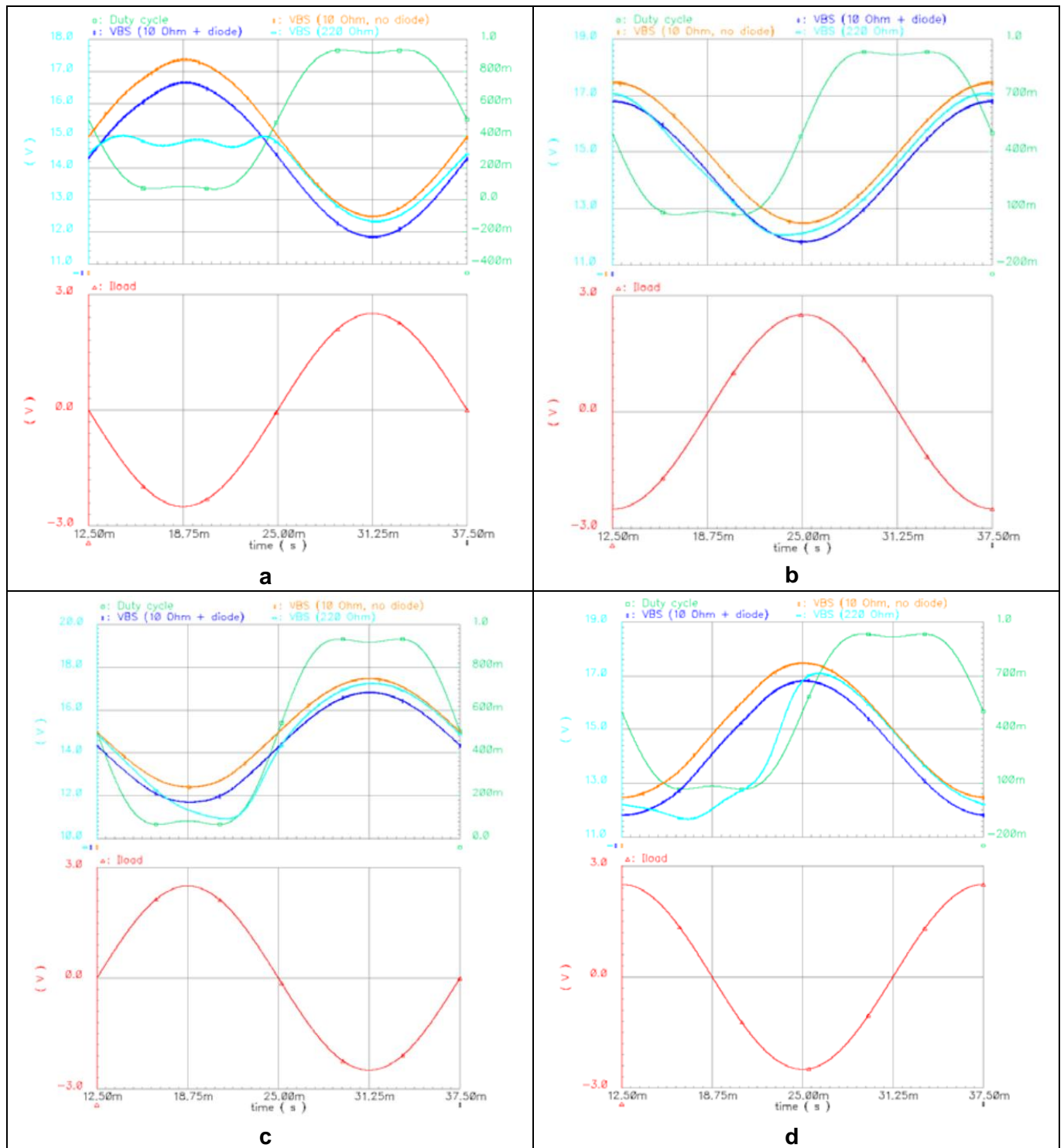
#### Equation 26

In this case we have the highest value for  $V_{BSMAX}$ .  $I_{LOAD}$  flows into the free-wheeling diode, the voltage drop of which increases the available voltage for charging  $V_{BS}$ . The same consideration can be made for  $I_{LOAD} < 0$ , but in this case the phenomenon happens when the duty cycle is at a minimum (which helps by increasing  $V_{BSMAX}$ ).

Figure 16 shows the result of a simulation where the load current is phase shifted with the applied voltage. The plots show the duty cycle (green), simulated  $V_{BS}$  voltage (blue = 200  $\Omega$  bootstrap resistor, Cyan = 10  $\Omega$  bootstrap resistor + diode, Orange = maximum achievable  $V_{BS}$ ) and the load current (red) positive entering the phase.

# Bootstrap Network Analysis: Focusing on the Integrated Bootstrap Functionality

Considering the bootstrap circuit for varying loads



**Figure 16** Integrated bootstrap circuitry in parallel with external Bootstrap components (5  $\mu$ s min pulse)

## Considering the bootstrap circuit for varying loads

- $I_{QBS} = 150 \mu A$ ;
- $I_{LK} = 50 \mu A$ ;
- $Q_{LS} = 1.2 \text{ nC}$ ;
- $Q_G = 40 \text{ nC}$ ;
- $T_S = 50 \mu s$  ( $f=20 \text{ kHz}$ );
- $V_F=1 \text{ V}$ ;
- $R_{boot} = 220 \Omega$ ;
- $V_{CC} = 15 \text{ V}$ ;
- $V_{CEon} = 3 \text{ V}$ ;
- $V_{GEmin} = 10 \text{ V}$ ; and
- $D_{MIN}=10\%$  (minimum duty cycle of the PWM carrier).

The schematic of the simulation is a modification of the circuit shown in Figure 2, to allow us to consider the effects of  $V_{CEON}$  and  $V_{FP}$  (that have been idealized as having a sinusoidal shape).

Now we'll examine a series of test measurements that help us understand the  $V_{BS}$  behavior as a function of both modulation and current phase lag with voltage. The test conditions are shown below (slightly different from previous test conditions).

- PWM=20 kHz
- $C_{boot}=1 \mu F$
- Fundamental= 11 Hz
- Minimum pulse = 367 ns ( $m=98.5\%$ )
- Load current (positive toward the inverter stage)= 5 A peak-peak,

# Bootstrap Network Analysis: Focusing on the Integrated Bootstrap Functionality

Considering the bootstrap circuit for varying loads

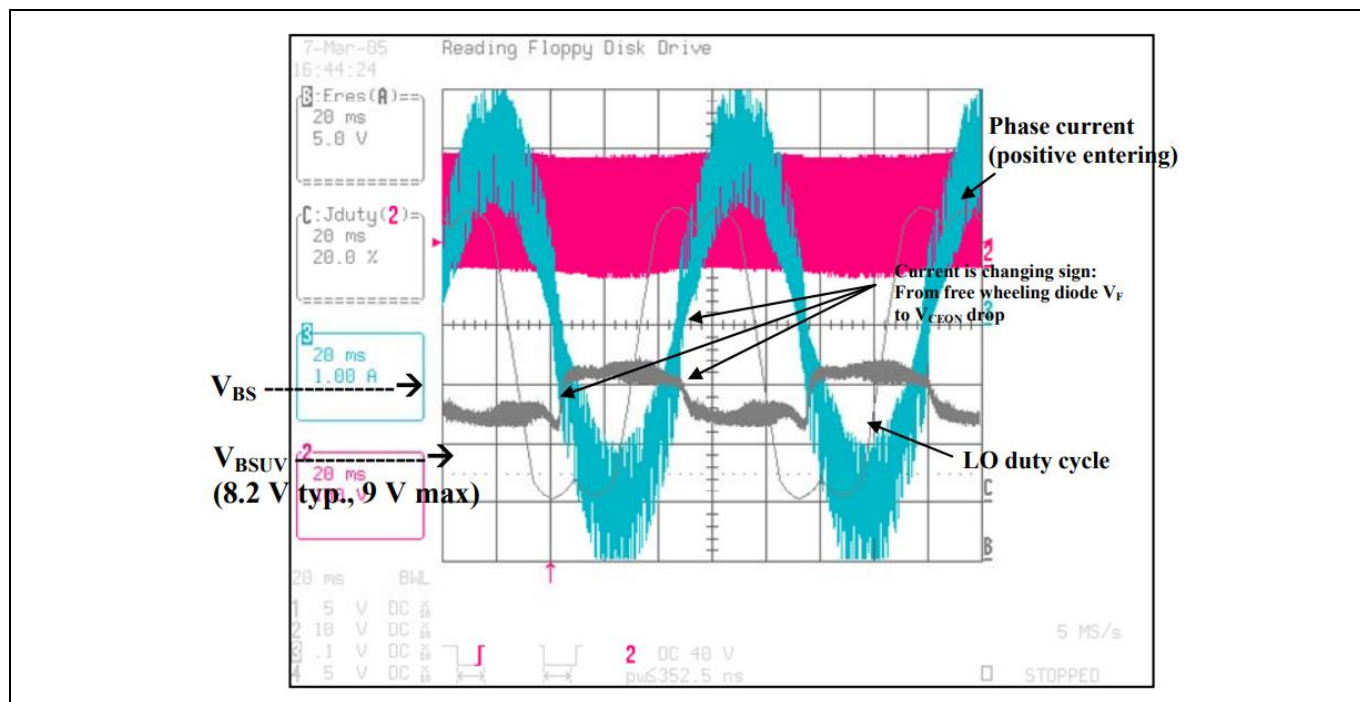


Figure 17 10  $\Omega$  + external diode bootstrap circuit

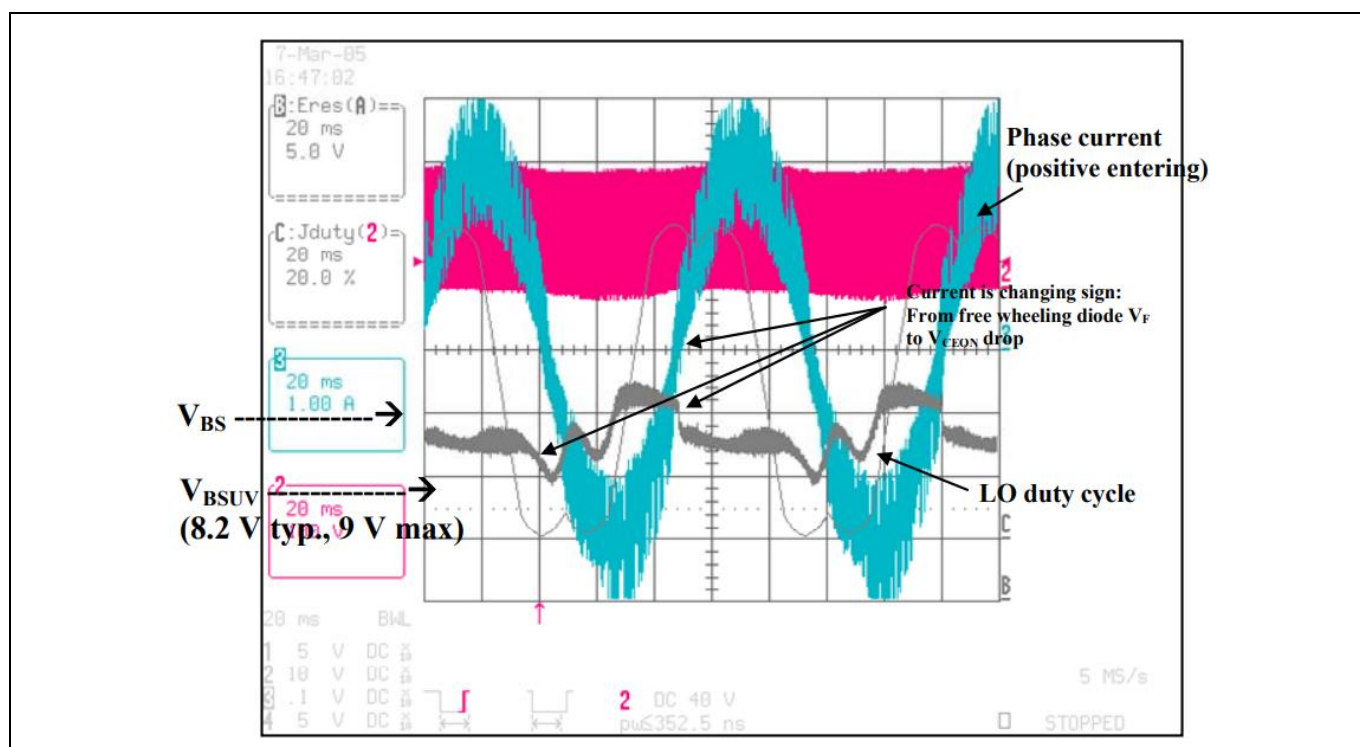


Figure 18 Integrated bootstrap circuitry

Considering the bootstrap circuit for varying loads

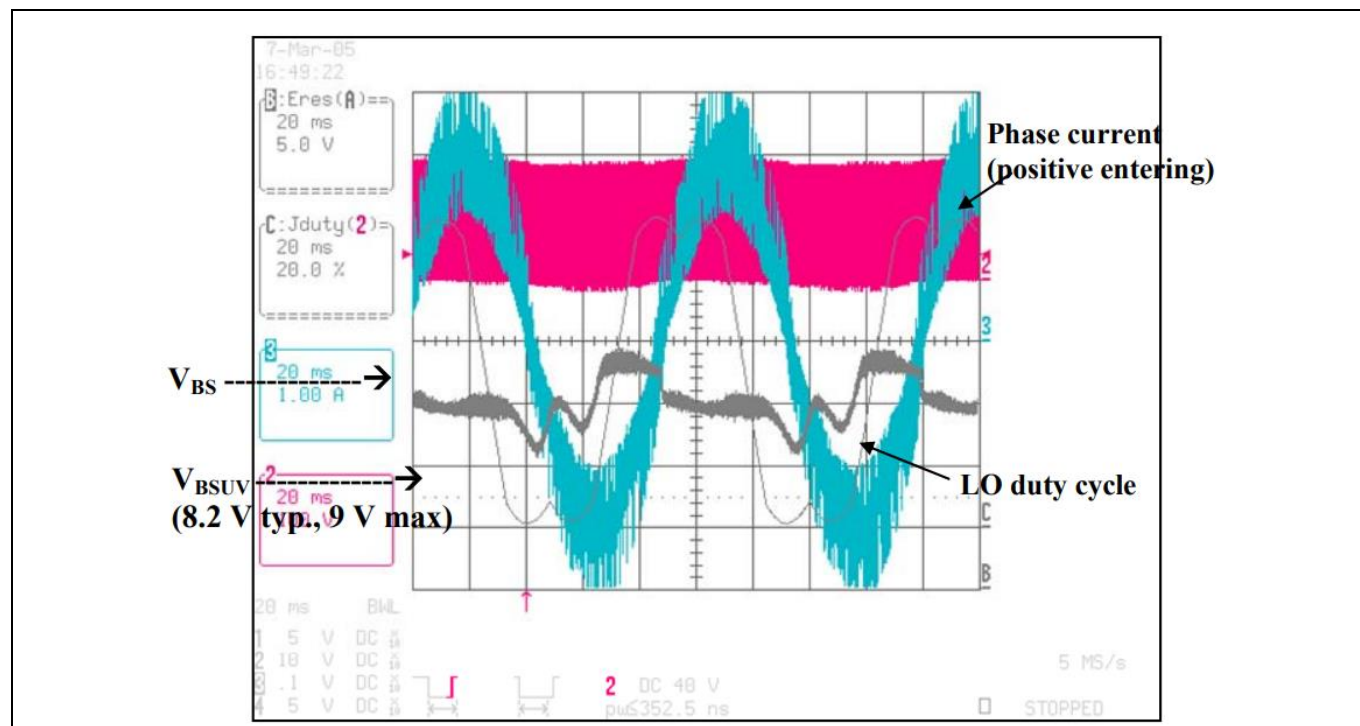


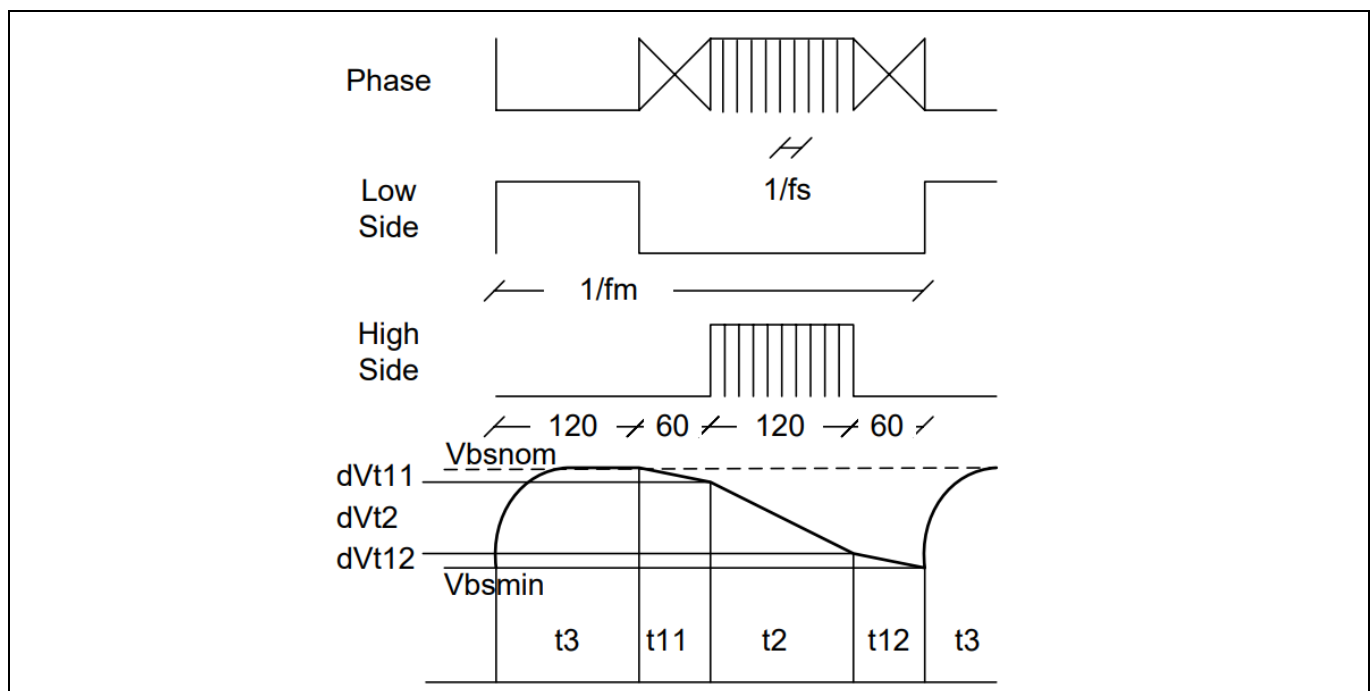
Figure 19 Integrate bootstrap circuitry with 17 V  $V_{CC}$  supply

## Limitations of the integrated bootstrap

### 6 Limitations of the integrated bootstrap

The integrated bootstrap FET considered above follows the assumption that the bootstrap FET is turned on only when LO is active (and the  $V_S$  pin is tied to  $V_{SS}$ ). This working principle leads to a waste of the deadtime period, which can be used for recharging the bootstrap capacitor during low-side freewheeling recirculation. The Infineon parts that features an integrated bootstrap diode does not suffer from this issue. In most cases, (motor drive applications usually have a max switching frequency of around 20 kHz, with deadtime periods less than 3  $\mu$ s), the resulting loss of charge is negligible.

A second limitation, which is related to the integrated bootstrap is for non-complementary switching schemes.



**Figure 20 Behavior of  $V_{BS}$  voltage for 6-step non-complementary switching scheme**

As an example, we considered the 6-step switching scheme with the high-side IGBT chopped while the low-side IGBT remains off (see Figure 20).  $V_{BS}$  charges only during the period in which low-side IGBT is on ( $t_3$ ) and the  $C_{boot}$  charge is never refreshed during high side switching period ( $t_2$ ).

A way to overcome this problem is, while chopping the high-side switch, to switch the low-side in a complementary way; this will allow a refresh of the bootstrap capacitor. In the case of complementary switching, the equations developed in section 2 apply.

Infineon provides also devices with a different integrated bootstrap turn-on strategy, which are suitable for non-complementary PWM schemes. This topic is not discussed in this application note.



## Conclusions

### 7 Conclusions

We considered the effects of the bootstrap resistor and capacitor on the charge of the floating supply. The main issue introduced by the resistive bootstrap circuit is an average voltage drop that impacts the minimum duty cycle obtainable for the application. Examples have been shown that this effect is not preventing the use of integrated bootstrap topology for sinusoidal drive.

The equations that have been obtained are valid in general, and must be verified by the use to determine if the integrated bootstrap topology can match the design requirements.

This Application Note mainly describes applications which use the 3-phase space vector (or 3-phase sinusoidal + 3<sup>rd</sup> harmonic) modulation. Other kinds of modulations (e.g., 2-phase space vector, 6-step, etc.) have to be considered separately.

Low cost applications can benefit from the integration of the bootstrap functionality by reducing the number of external components (3 HV diodes + 1 resistor) and saving space on the board. This solution can be particularly appealing to modules that utilize a high degree of integration.



## References

## References

[1] IR2136S datasheet: <https://www.infineon.com/cms/en/product/power/gate-driver-ics/ir2136s/>

**Revision history**

**Revision history**

Document revision	Date	Description of changes
Revision 1.00		Initial Version
Revision 1.01	2024-11-20	Document Template Change

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